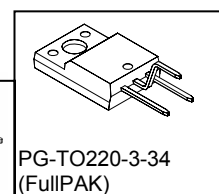
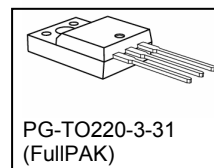
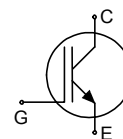


HighSpeed 2-Technology

- **Designed for:**
 - TV – Horizontal Line Deflection
- **2nd generation HighSpeed-Technology for 1200V applications offers:**
 - loss reduction in resonant circuits
 - temperature stable behavior
 - parallel switching capability
 - tight parameter distribution
 - E_{off} optimized for $I_C = 3A$
 - simple Gate-Control
- Qualified according to JEDEC¹ for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	V_{CE}	I_C	E_{off}	$T_{j,max}$	Marking	Package
IGA03N120H2	1200V	3A	0.15mJ	150°C	G03H1202	PG-TO-220-3-31
IGA03N120H2	1200V	3A	0.15mJ	150°C	G03H1202	PG-TO-220-3-34

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1200	V
Triangular collector peak current ($V_{GS} = 15V$) $T_C = 100^\circ C, f = 32kHz$	I_{Cpk}	8.2	A
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	9	
Turn off safe operating area $V_{CE} \leq 1200V, T_j \leq 150^\circ C$	-	9	
Gate-emitter voltage	V_{GE}	± 20	V
Power dissipation $T_C = 25^\circ C$	P_{tot}	29	W
Operating junction and storage temperature	T_j, T_{stg}	-40...+150	°C
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	
Isolation Voltage	V_{isol}	2500	V_{rms}

¹ J-STD-020 and JESD-022

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		4.3	K/W
Thermal resistance, junction – ambient	R_{thJA}		64	

Electrical Characteristic, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=300\mu A$	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=3A$ $T_j=25^\circ C$	-	2.2	2.8	
		$T_j=150^\circ C$ $V_{GE} = 10V, I_C=3A,$ $T_j=25^\circ C$	-	2.5	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=90\mu A, V_{CE}=V_{GE}$	2.1	3	3.9	
Zero gate voltage collector current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V$ $T_j=25^\circ C$	-	-	20	μA
		$T_j=150^\circ C$	-	-	80	
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE}=20V, I_C=3A$	-	2	-	S
Dynamic Characteristic						
Input capacitance	C_{iss}	$V_{CE}=25V$ $V_{GE}=0V$ $f=1MHz$	-	205	-	pF
Output capacitance	C_{oss}		-	24	-	
Reverse transfer capacitance	C_{riss}		-	7	-	
Gate charge	Q_{Gate}	$V_{CC}=960V, I_C=3A$ $V_{GE}=15V$	-	8.6	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	7	-	nH

Switching Characteristic, Inductive Load, at $T_j=25^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}$	-	9.2	-	ns
Rise time	t_r	$V_{CC}=800\text{V}, I_C=3\text{A}$	-	5.2	-	
Turn-off delay time	$t_{d(off)}$	$V_{GE}=0\text{V}/15\text{V}$	-	281	-	
Fall time	t_f	$R_G=82\Omega$	-	29	-	mJ
Turn-on energy	E_{on}	$L_\sigma^{(2)}=180\text{nH}$	-	0.14	-	
Turn-off energy	E_{off}	$C_\sigma^{(1)}=40\text{pF}$	-	0.15	-	
Total switching energy	E_{ts}	Energy losses include "tail" and diode ²⁾ reverse recovery.	-	0.29	-	

Switching Characteristic, Inductive Load, at $T_j=150^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ\text{C}$	-	9.4	-	ns
Rise time	t_r	$V_{CC}=800\text{V}, I_C=3\text{A}$	-	6.7	-	
Turn-off delay time	$t_{d(off)}$	$V_{GE}=0\text{V}/15\text{V}$	-	340	-	
Fall time	t_f	$R_G=82\Omega$	-	63	-	mJ
Turn-on energy	E_{on}	$L_\sigma^{(1)}=180\text{nH}$	-	0.22	-	
Turn-off energy	E_{off}	$C_\sigma^{(1)}=40\text{pF}$	-	0.26	-	
Total switching energy	E_{ts}	Energy losses include "tail" and diode ³⁾ reverse recovery.	-	0.48	-	

Switching Energy ZVT, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-off energy	E_{off}	$V_{CC}=800\text{V}, I_C=3\text{A}$ $V_{GE}=0\text{V}/15\text{V}$ $R_G=82\Omega, C_r^{(1)}=4\text{nF}$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	0.05 0.09	-	mJ

²⁾ Leakage inductance L_σ and stray capacity C_σ due to dynamic test circuit in figure E

³⁾ Commutation diode from device IKP03N120H2

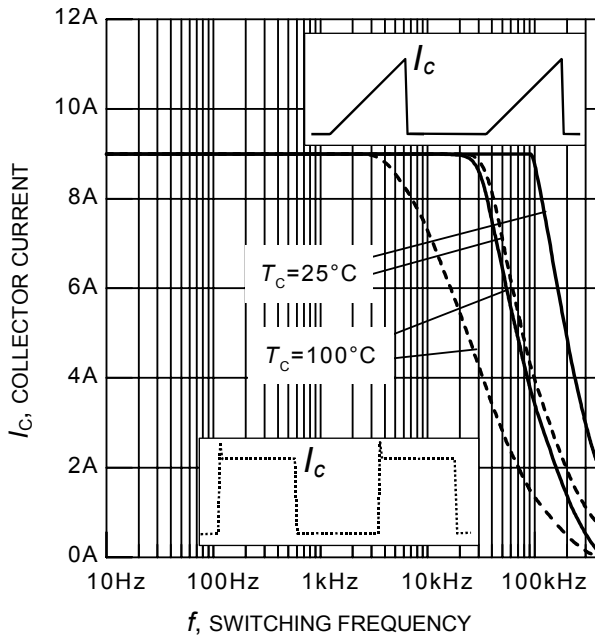


Figure 1. Collector current as a function of switching frequency
 ($T_j \leq 150^\circ\text{C}$, $D = 0.5$, $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $R_G = 82\Omega$)

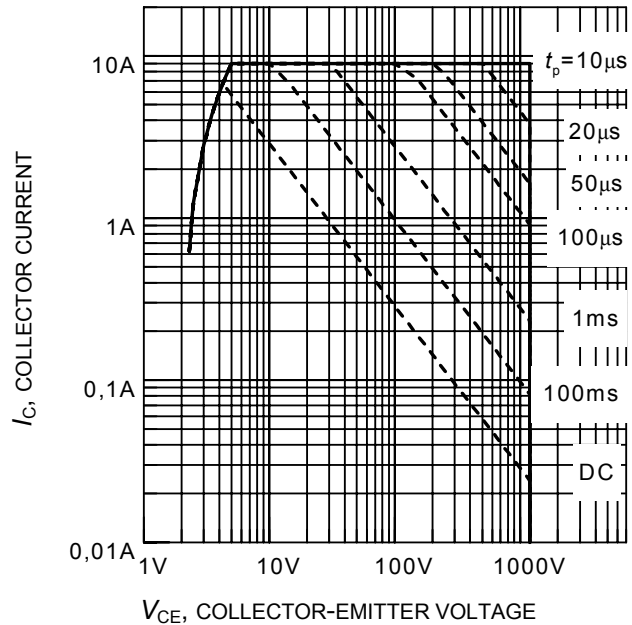


Figure 2. Safe operating area
 ($D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$)

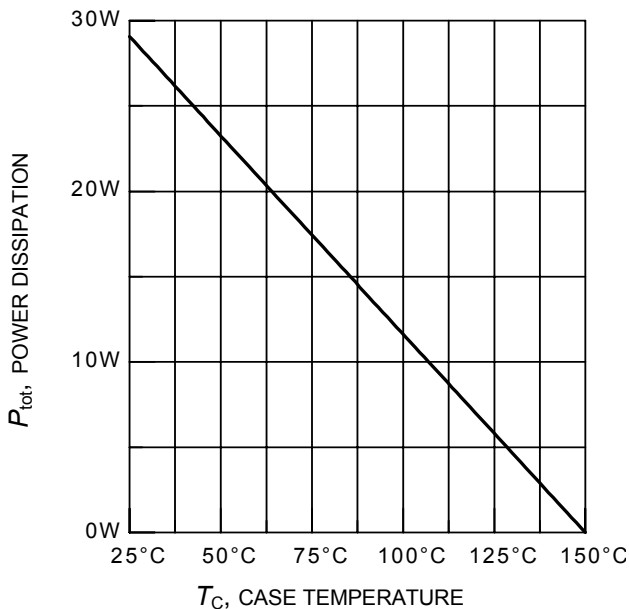


Figure 3. Power dissipation as a function of case temperature
 ($T_j \leq 150^\circ\text{C}$)

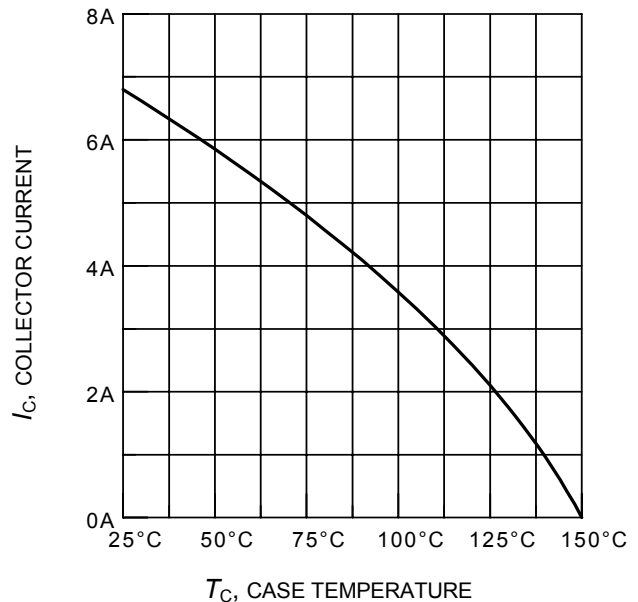


Figure 4. Collector current as a function of case temperature
 ($V_{GE} \leq 15\text{V}$, $T_j \leq 150^\circ\text{C}$)

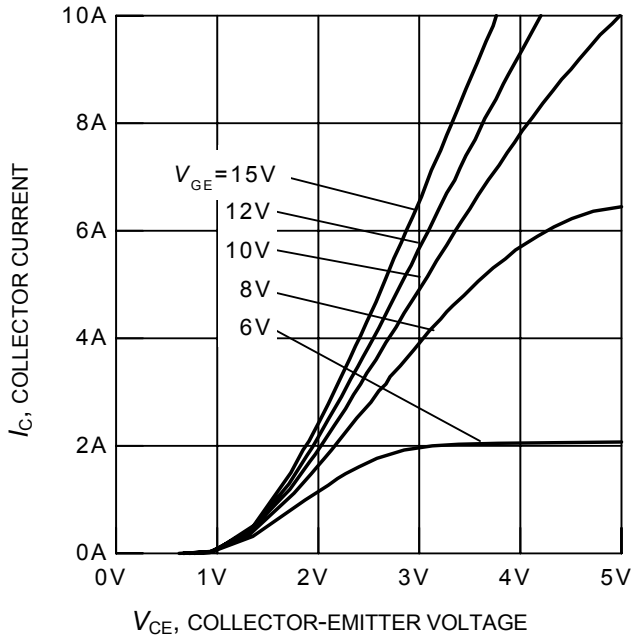


Figure 5. Typical output characteristics
($T_j = 25^\circ\text{C}$)

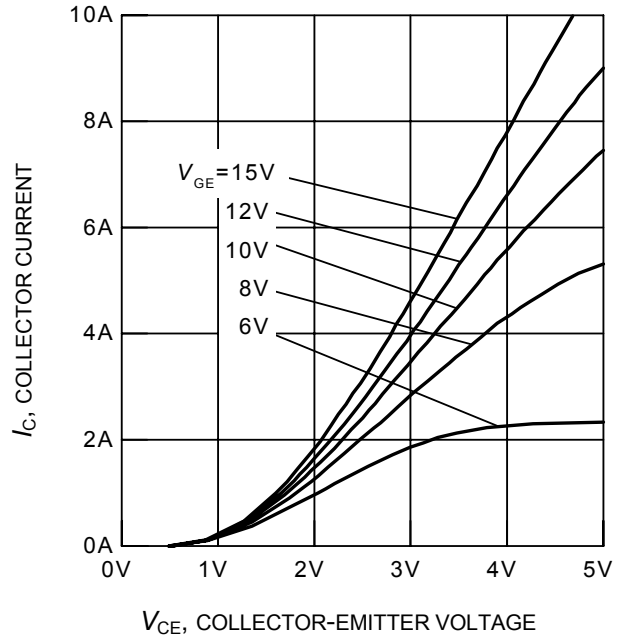


Figure 6. Typical output characteristics
($T_j = 150^\circ\text{C}$)

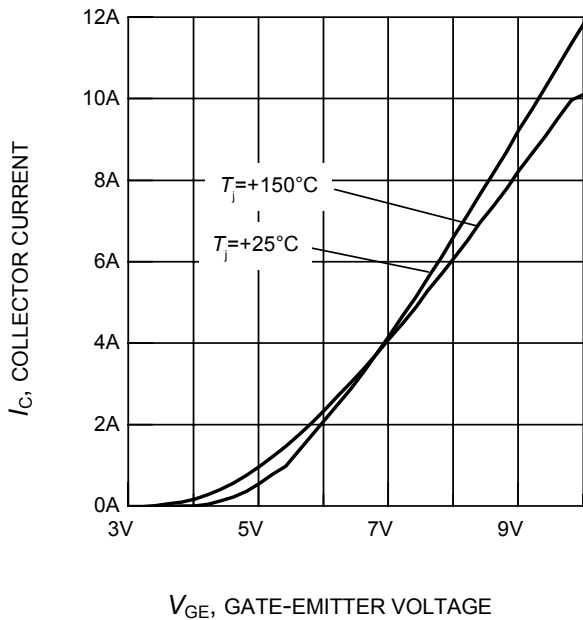


Figure 7. Typical transfer characteristics
($V_{CE} = 20\text{V}$)

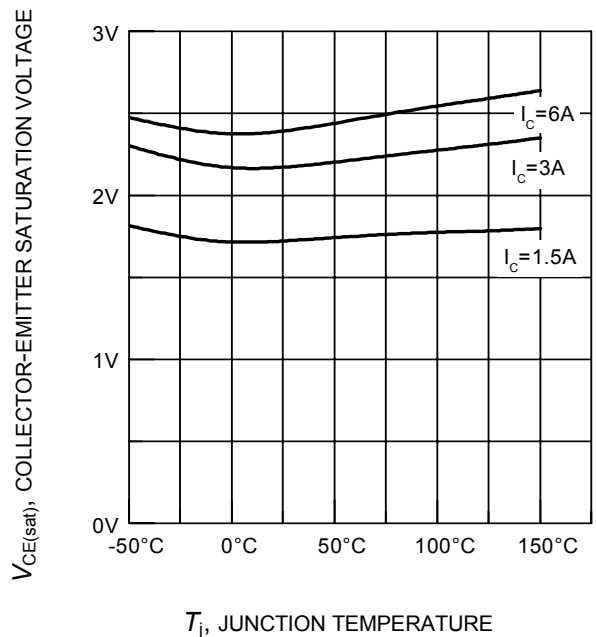
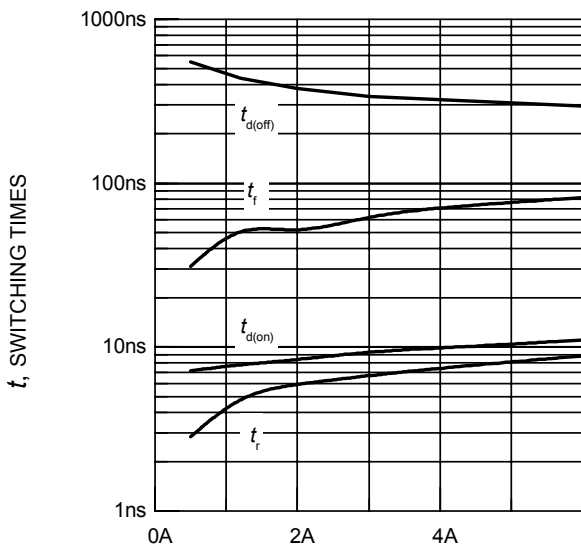


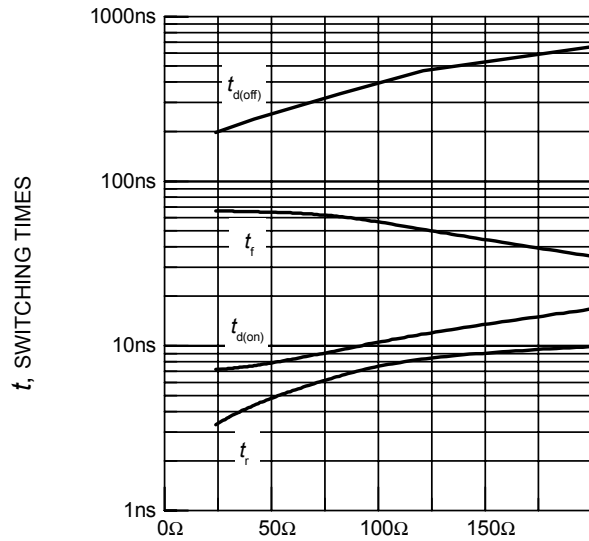
Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 15\text{V}$)



I_C , COLLECTOR CURRENT

Figure 9. Typical switching times as a function of collector current

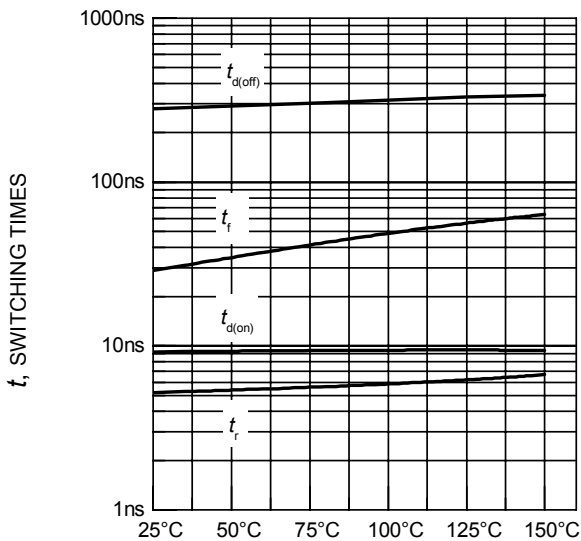
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $R_G = 82\Omega$, dynamic test circuit in Fig.E)



R_G , GATE RESISTOR

Figure 10. Typical switching times as a function of gate resistor

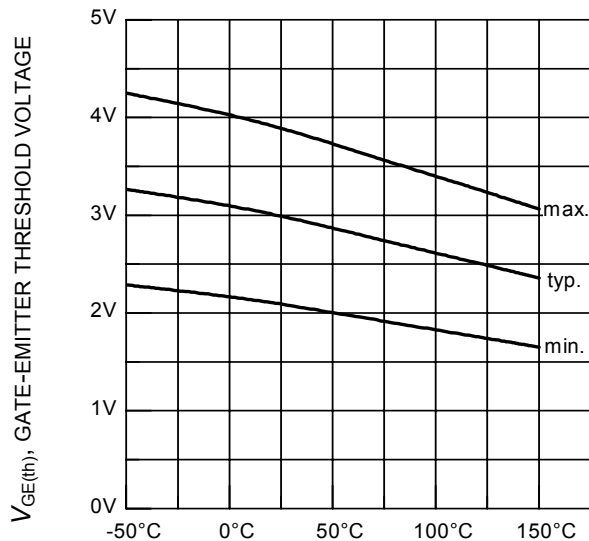
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $I_C = 3\text{A}$, dynamic test circuit in Fig.E)



T_j , JUNCTION TEMPERATURE

Figure 11. Typical switching times as a function of junction temperature

(inductive load, $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $I_C = 3\text{A}$, $R_G = 82\Omega$, dynamic test circuit in Fig.E)



T_j , JUNCTION TEMPERATURE

Figure 12. Gate-emitter threshold voltage as a function of junction temperature

($I_C = 0.09\text{mA}$)

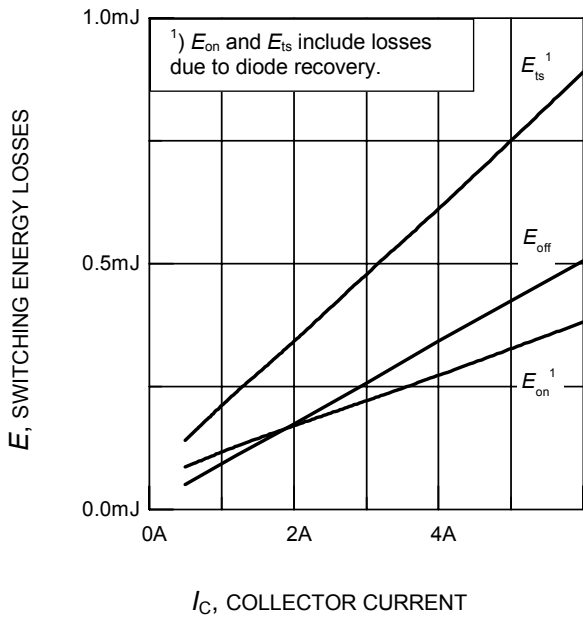


Figure 13. Typical switching energy losses as a function of collector current
 (inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $R_G = 82\Omega$, dynamic test circuit in Fig.E)

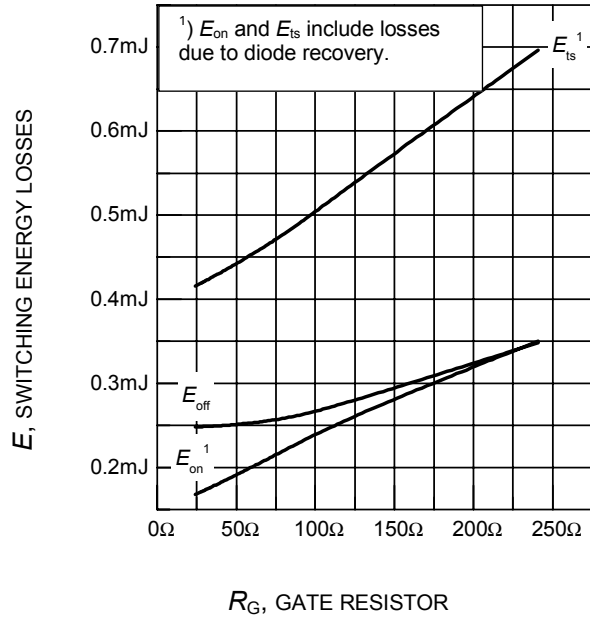


Figure 14. Typical switching energy losses as a function of gate resistor
 (inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $I_C = 3\text{A}$, dynamic test circuit in Fig.E)

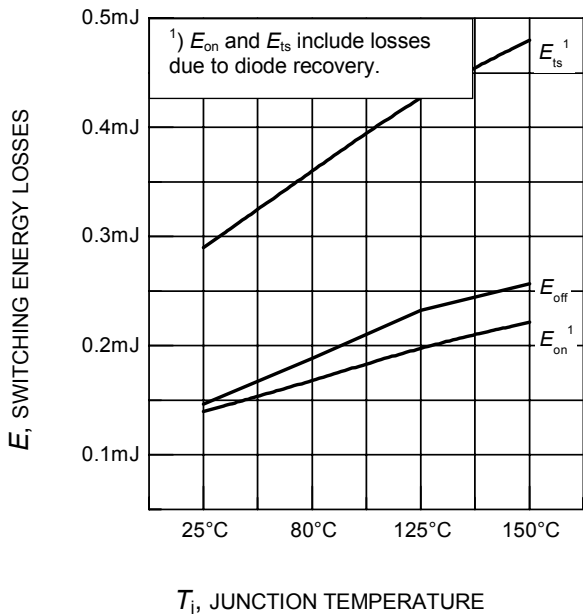


Figure 15. Typical switching energy losses as a function of junction temperature
 (inductive load, $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $I_C = 3\text{A}$, $R_G = 82\Omega$, dynamic test circuit in Fig.E)

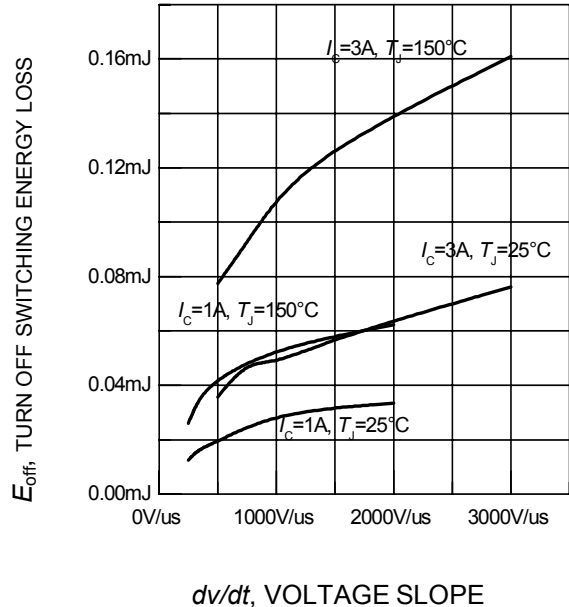
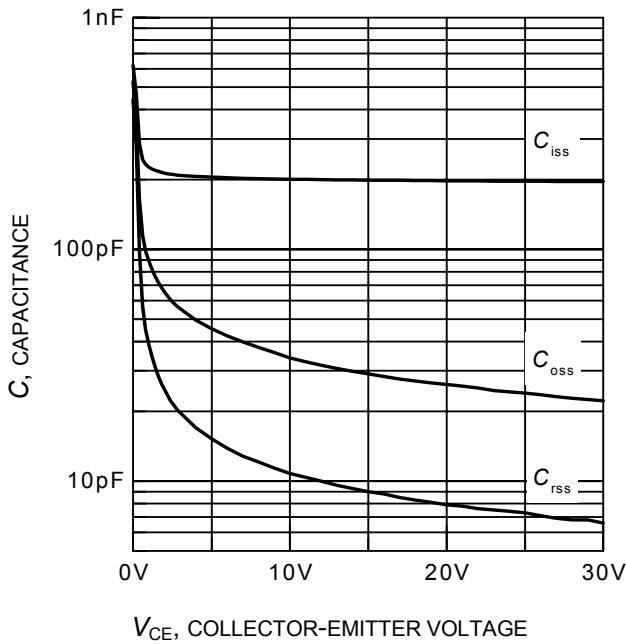
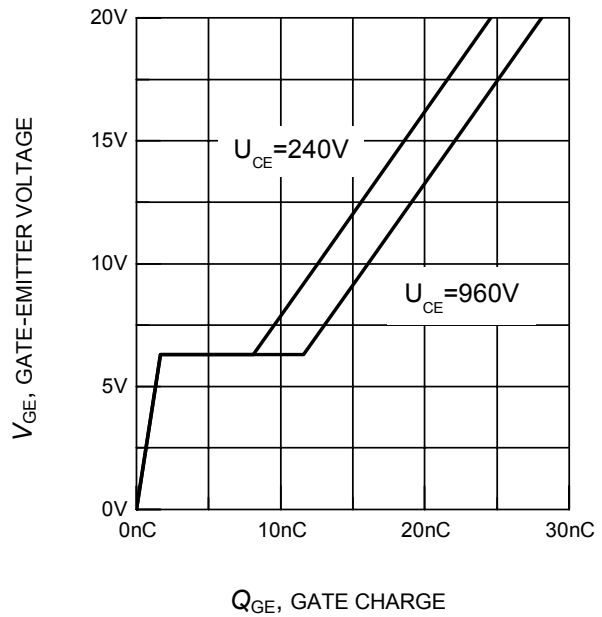


Figure 16. Typical turn off switching energy loss for soft switching
 (dynamic test circuit in Fig. E)



V_{CE} , COLLECTOR-EMITTER VOLTAGE
Figure 19. Typical capacitance as a function of collector-emitter voltage
 ($V_{GE} = 0V, f = 1MHz$)



Q_{GE} , GATE CHARGE
Figure 18. Typical gate charge
 ($I_C = 3A$)

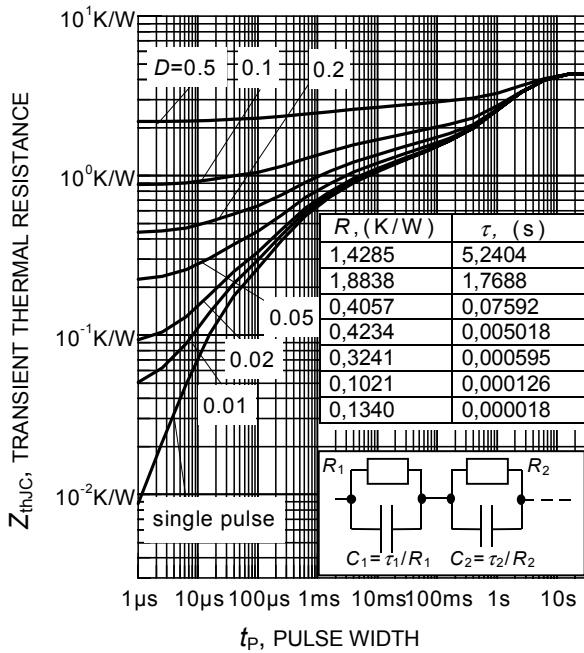
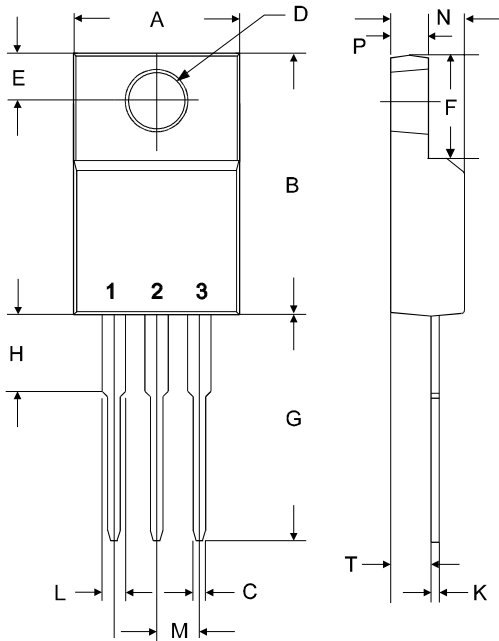


Figure 17. IGBT transient thermal impedance as a function of pulse width
 ($D = t_p / T$)

PG-TO-220-3-31 (FullPAK)


symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	10.37	10.63	0.4084	0.4184
B	15.86	16.12	0.6245	0.6345
C	0.65	0.78	0.0256	0.0306
D	2.95 typ.		0.1160 typ.	
E	3.15	3.25	0.124	0.128
F	6.05	6.56	0.2384	0.2584
G	13.47	13.73	0.5304	0.5404
H	3.18	3.43	0.125	0.135
K	0.45	0.63	0.0177	0.0247
L	1.23	1.36	0.0484	0.0534
M	2.54 typ.		0.100 typ.	
N	4.57	4.83	0.1800	0.1900
P	2.57	2.83	0.1013	0.1113
T	2.51	2.62	0.0990	0.1030

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